

Page 22, line 16, change "dyne/cm<sup>2</sup>" to read --dyne/cm--.

Page 23, line 1, change "dyne/cm<sup>2</sup>" to read --dyne/cm--; and

line 3, change "dyne/cm<sup>2</sup>" to read --dyne/cm--.

Page 25, line 1, change "dyne/cm<sup>2</sup>" to read --dyne/cm--; and

line 7, change "dyne/cm<sup>2</sup>" to read --dyne/cm--, both

NE instances.

Page 32, line 18, change "dyne/cm<sup>2</sup>" to read --dyne/cm--.

Page 33, line 7, change "dyne/cm<sup>2</sup>" to read --dyne/cm--;

line 10, change "dyne/cm<sup>2</sup>" to read --dyne/cm--;

line 16, change "dyne/cm<sup>2</sup>" to read --dyne/cm--; and

line 17, change "dyne/cm<sup>2</sup>" to read --dyne/cm--.

IN THE CLAIMS:

Please rewrite claims 33 and 37 as follows:

33. (twice amended) A stress-adjusted insulating film forming method for forming a multilayered insulating film on a substrate, said method comprising the steps of:

(a) forming a first insulating layer with a first type of [tensile] stress;

(b) forming a second insulating layer with a second type of [compressive] stress, different from said first type of stress;

(c) forming a conductive interconnection layer on and in contact with said second insulating layer;

(d) forming a third insulating layer with said second type of



[compressive] stress on and in contact with said conductive interconnection layer; and

(e) repeating steps (a) through (d) at least twice to produce a structure containing at least three of said conductive interconnection layers, each of said conductive interconnection layers being sandwiched between and having opposing surfaces in contact with insulating layers having the same type of [compressive] stress.

37. (twice amended) A semiconductor device comprising a substrate, a plurality of first and second types of insulating films having, respectively, compressive and tension stress formed on said substrate and at least three layers of conductive interconnectors sandwiched between and in contact with insulating films having the same type of [compressive] stress.

Claim 40, line 3, delete "dyne/cm<sup>2</sup>" and insert "--dyne/cm--".

Please add the following new claims:

--41. A method according to claim 33 wherein said first type of stress is tensile stress and said second type of stress is compressive stress.

42. A semiconductor device according to claim 37 wherein said first type of stress is tensile stress, said second type of stress